Product data sheet

1. General description

High-voltage, high-speed planar-passivated NPN power switching transistor in a SOT78 (TO-220AB) plastic package.

2. Features and benefits

- · Low thermal resistance
- Fast switching

3. Applications

- Inverters
- Motor control systems
- Electronic lighting ballasts
- DC-to-DC converters

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Values			Unit	
Absolute	maximum rating		·				
V_{CESM}	peak collector-emitter voltage	V _{BE} = 0 V	700			V	
I _C	collector current (DC)		4			А	
P _{tot}	total power dissipation	T _{mb} ≤ 25 °C; <u>Fig. 1</u>	80		W		
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static ch	aracteristics						
h _{FE}	DC current gain	I _C = 1 A; V _{CE} = 5 V; T _{mb} = 25 °C; Fig. 9		10	17	32	
		$I_{C} = 500 \text{ mA}; V_{CE} = 5 \text{ V}; T_{mb} = 25 \text{ °C}$		13	22	32	

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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	mb	
2	С	collector	1 7 9	2
3	Е	emitter		1
mb	С	mounting base; connected to collector		3 sym056

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUJ103A	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

7. Marking

Table 4. Marking codes

Type number	Marking codes
BUJ103A	BUJ103A

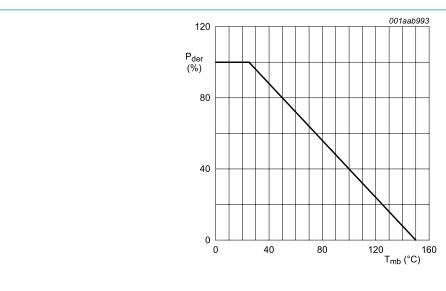
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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{CESM}	peak collector-emitter voltage	V _{BE} = 0 V	700	V
V_{CBO}	collector-base voltage	open emitter	700	V
V_{CEO}	collector-emitter voltage	open base	400	V
I _c	collector current (DC)		4	Α
I _{CM}	peak collector current		8	Α
I _B	base current (DC)		2	Α
I _{BM}	peak base current		4	Α
P _{tot}	total power dissipation	T _{mb} ≤ 25 °C; <u>Fig. 1</u>	80	W
T _{stg}	storage temperature		-65 to 150	°C
T _j	junction temperature		150	°C



 $P_{der}(\%) = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$

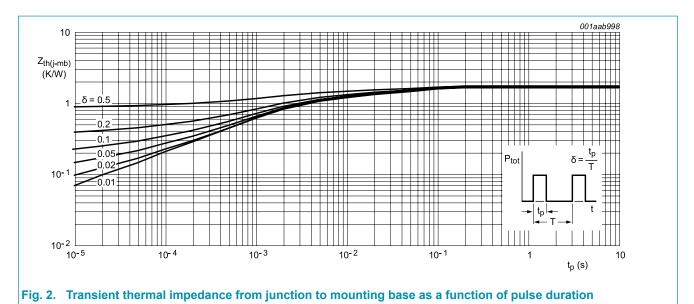
Fig. 1. Normalized total power dissipation as a function of mounting base temperature

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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 2	-	-	1.56	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	-	60	-	K/W



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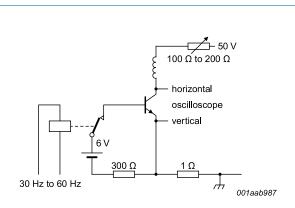
10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics			'		
I _{CES} collector-emitter cut-off		V _{BE} = 0 V; V _{CE} = V _{CESMmax} ; T _{mb} = 25 °C; [1]	-	-	1	mA
	current	V _{BE} = 0 V; V _{CE} = V _{CESMmax} ; T _j = 125 °C; [1]	-	-	2	mA
I _{CBO}	collector-base cut-off current	$V_{BE} = 0 \text{ V; } V_{CE} = V_{CESMmax}; T_{mb} = 25 \text{ °C; [1]}$	-	-	1	mA
I _{CEO}	collector-emitter cut-off current	V _{CEO} = V _{CEOMmax} = 400 V; T _{mb} = 25 °C; [1]	-	-	0.1	mA
I _{EBO}	emitter-base cut-off current	$V_{EB} = 7 \text{ V; } I_{C} = 0 \text{ A; } T_{mb} = 25 \text{ °C}$	-	-	0.1	mA
V_{CEOsus}	collector-emitter sustaining voltage	I _B = 0 A; I _C = 10 mA; L = 25 mH; T _{mb} = 25 °C; <u>Fig. 3</u> ; <u>Fig. 4</u>	400	-	-	V
V_{CEsat}	collector-emitter saturation voltage	I_{C} = 3.0 A; I_{B} = 0.6 A; T_{mb} = 25 °C; Fig. 10	-	0.25	1	V
V_{BEsat}	base-emitter saturation voltage	$I_{C} = 3.0 \text{ A}; I_{B} = 0.6 \text{ A}; T_{mb} = 25 \text{ °C};$ Fig. 11	-	0.97	1.5	V
h _{FE}	DC current gain	I _C = 1 mA; V _{CE} = 5 V; T _{mb} = 25 °C; Fig. 9	10	17	32	
		$I_{\rm C}$ = 500 mA; $V_{\rm CE}$ = 5 V; $T_{\rm mb}$ = 25 °C	13	22	32	
h _{FEsat}		I _C = 2.0 A; V _{CE} = 5 V; T _{mb} = 25 °C	11	16	22	
gain		I _C = 3.0 A; V _{CE} = 5 V; T _{mb} = 25 °C	-	12.5	-	
Dynamic	characteristics			'		
Switching	g times (resistive load); Fig.	5; <u>Fig. 6</u>				
t _{on}	turn-on time	I_{Con} = 2.5 A; I_{Bon} = - I_{Boff} = 0.5 A; R_L = 75 Ω; T_{mb} = 25 °C	-	0.52	0.6	μs
t_{stg}	storage time	$I_{Con} = 2.5 \text{ A}; I_{Bon} = -I_{Boff} = 0.5 \text{ A}; R_L = 75 \Omega;$ $T_{mb} = 25 \text{ °C}$	-	2.7	3.3	μs
t _f	fall time	$I_{Con} = 2.5 \text{ A}; I_{Bon} = -I_{Boff} = 0.5 \text{ A}; R_L = 75 \Omega;$ $T_{mb} = 25 \text{ °C}$	-	0.3	0.35	μs
Switching	g times (inductive load);	<u>. 7; Fig. 8</u>				
t_{stg}	storage time	$I_{Con} = 2 \text{ A}; I_{Bon} = 0.4 \text{ A}; L_{B} = 1 \mu\text{H};$ $V_{BB} = -5 \text{ V}; T_{mb} = 25 \text{ °C}$	-	1.2	1.4	μs
t _f	fall time	I _{Con} = 2 A; I _{Bon} = 0.4 A; L _B = 1 μH; V _{BB} = -5 V; T _{mb} = 25 °C	-	30	60	ns
Switching	g times (inductive load);	. 7; <u>Fig. 8</u>				
t _{stg}	storage time	I _{Con} = 2 A; I _{Bon} = 0.4 A; L _B = 1 μH; V _{BB} = -5 V; T _j = 100 °C; T _{mb} = 25 °C	-	-	1.8	μs
t _f	fall time	I _{Con} = 2 A; I _{Bon} = 0.4 A; L _B = 1 μH; V _{BB} = -5 V; T _i = 100 °C; T _{mb} = 25 °C	-	-	120	ns

^[1] Measured with half sine-wave voltage (curve tracer).

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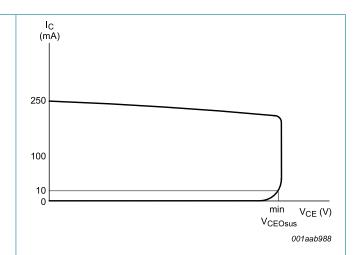
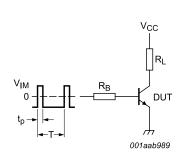
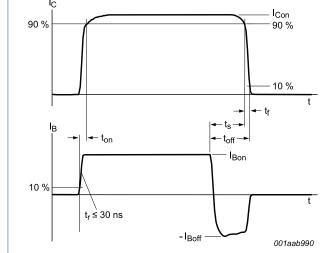


Fig. 3. Test circuit for collector-emitter sustaining voltage

Fig. 4. Oscilloscope display for collector-emitter sustaining voltage test waveform



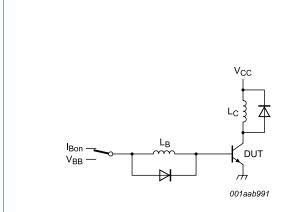


 V_{IM} = -6 V to +8 V; V_{CC} = 250 V; t_p = 20 $\mu s;$ δ = $t_p/$ T = 0.01 R_B and R_L calculated from I_{Con} and I_{Bon} requirements

Fig. 6. Switching times waveforms for resistive load

Fig. 5. Test circuit for resistive load switching

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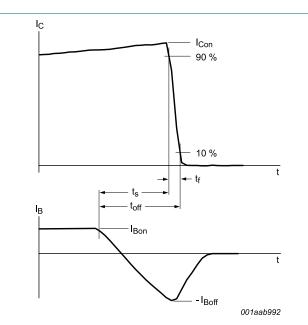


Fig. 8. Switching times waveforms for inductive load



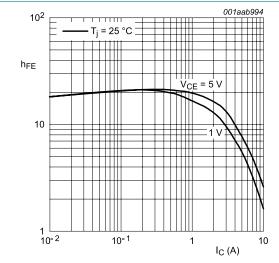
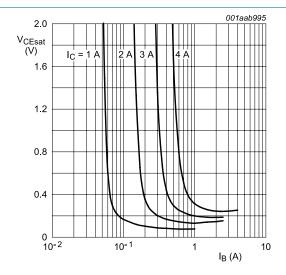


Fig. 9. DC current gain as a function of collector current; typical values



 T_j = 25 °C Fig. 10. Collector-emitter saturation voltage as a function of base current; typical values

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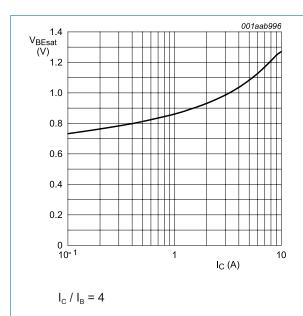
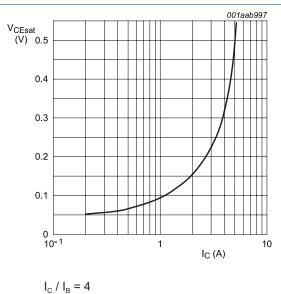
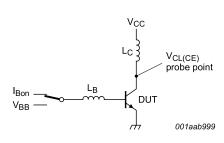


Fig. 11. Base-emitter saturation voltage as a function of collector current; typical values



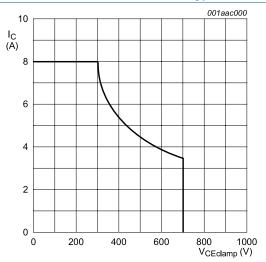
$$I_{\rm C} / I_{\rm B} = 4$$

Fig. 12. Collector-emitter saturation voltage as a function of collector current; typical values



$$\begin{split} &V_{\text{CEclamp}} \leq 1000 \text{ V; } V_{\text{CC}} = 150 \text{ V; } V_{\text{BB}} = \text{-}5 \text{ V; } \\ &L_{\text{B}} = 1 \text{ } \mu\text{H; } L_{\text{C}} = 200 \text{ } \mu\text{H} \end{split}$$

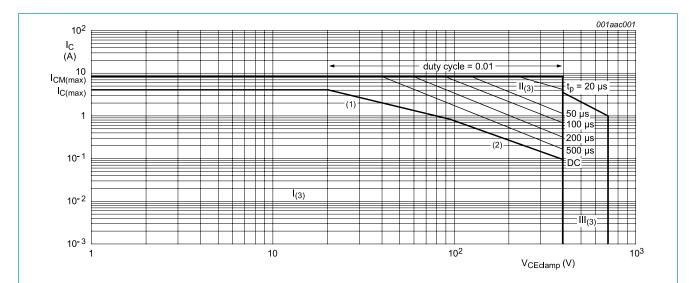
Fig. 13. Test circuit for reverse bias safe operating area



 $T_j \leq T_{j(max)}$

Fig. 14. Reverse bias safe operating area

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 $T_{mb} \le 25$ °C; Mounted with heatsink compound and 30 ± 5 Newton force on the center of the envelope.

- (1) P_{tot} maximum and P_{tot} peak maximum lines.
- (2) Second breakdown limits.
- (3) I = Region of permissible DC operation.
 - II = Extension for repetitive pulse operation.
 - III = Extension during turn-on in single transistor converters provided that $R_{BE} \le 100 \Omega$ and $t_p \le 0.6 \mu s$.

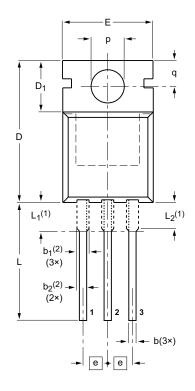
Fig. 15. Forward bias safe operating area

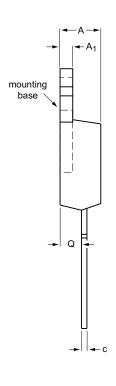
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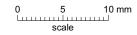
11. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

SOT78







DIMENSIONS (mm are the original dimensions)

UNIT	А	A ₁	b	b ₁ ⁽²⁾	b ₂ ⁽²⁾	С	D	D ₁	E	е	L	L ₁ ⁽¹⁾	L ₂ ⁽¹⁾ max.	р	q	Q
mm	4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2

Notes

- Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE	
SOT78		3-lead TO-220AB	SC-46		08-04-23 08-06-13	

BUJ103A

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12. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes					
BUJ103A v.5	20180329	Product data sheet	-	BUJ103A v.4					
Modifications:	Change from NXP version to WeEn version								
BUJ103A v.4	20111108	Product data sheet	-	BUJ103A v.3					
Modifications: • The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. • Legal texts have been adapted to the new company name where appropriate.									
BUJ103A v.3	20050303	Product data sheet	-	BUJ103A_HG v.2					
BUJ103A_HG v.2	19980918	Product data sheet	-	BUJ103A v.1					
BUJ103A v.1	19980801	Product data sheet	-	-					

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13. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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For sales office addresses, please send an email to: salesaddresses@ween-semi.com
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